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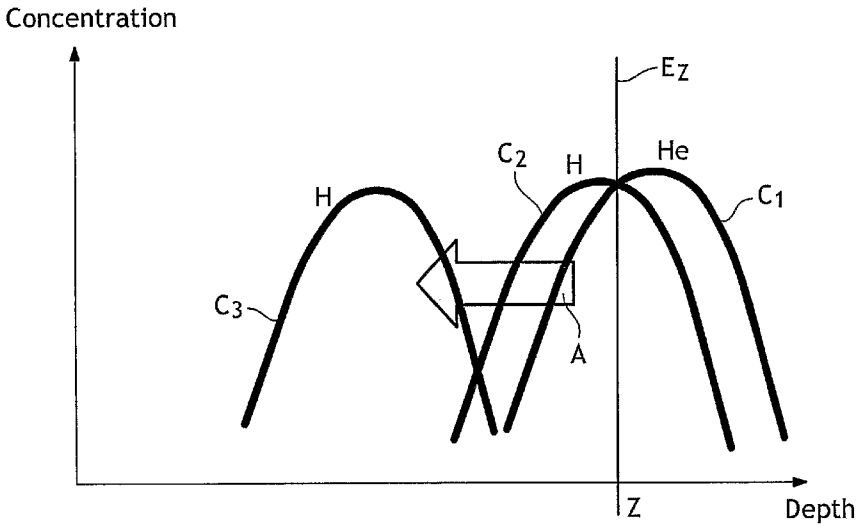
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(54) Title: METHOD FOR OBTAINING A THIN LAYER BY IMPLEMENTING CO-IMPLANTATION AND SUBSEQUENT IMPLANTATION



(57) Abstract: The invention proposes a method for transferring a thin layer of semiconductor material on a substrate by the SMARTCUT™ type process, the method being characterized in that the implantation step comprises: a first implantation operation consisting in carrying out an implantation of species so as to create said embrittlement zone at a first depth in the thickness of the donor substrate; a second implantation operation consisting in carrying out an implantation of species according to second implantation conditions chosen to create: - at a second depth different from said first depth so as not to affect the detachment that has to take place at the level of the embrittlement zone at said first depth, gettering region preventing the diffusion of species implanted during said first implantation operation towards said face of the donor substrate under which implantation is carried out, thus limiting blisters formation.

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